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TEXAS INSTRUMENTS

TLV9051, TLV9052, TLV9054

SBOS942H-AUGUST 2018-REVISED OCTOBER 2019

TLV9051 / TLV9052 / TLV9054 5-MHz, 15-V/µs High Slew-Rate, RRIO Op Amp

1 Features

- High slew rate: 15 V/µs
- Low quiescent current: 330 µA
- Rail-to-rail input and output
- Low input offset voltage: ±0.33 mV
- Unity-gain bandwidth: 5 MHz
- Low broadband noise: 15 nV/√Hz
- Low input bias current: 2 pA
- Unity-gain stable
- Internal RFI and EMI filter
- Scalable family of CMOS op amps for low-cost applications
- Operational at supply voltages as low as 1.8 V
- Extended temperature range: -40°C to 125°C

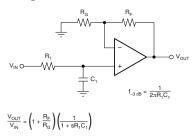
2 Applications

- HVAC: heating, ventilating, and air conditioning
- Photodiode amplifier
- Current shunt monitoring for DC motor control
- White goods (refrigerators, washing machines, and so forth)
- Sensor signal conditioning
- Active filters
- Low-side current sensing

3 Description

The TLV9051, TLV9052, and TLV9054 devices are single, dual, and quad operational amplifiers, respectively. The devices are optimized for low voltage operation from 1.8 V to 5.5 V. The inputs and outputs can operate from rail to rail at a very high slew rate. These devices are perfect for cost-constrained applications where low-voltage operation, high slew rate, and low quiescent current is needed. The capacitive-load drive of the TLV905x family is 150 pF, and the resistive open-loop output impedance makes stabilization easier with much higher capacitive loads.

Single-Pole, Low-Pass Filter



The TLV905xS devices include a shutdown mode that allow the amplifiers to be switched off into a standby mode with typical current consumption less than 1 μ A.

The TLV905x family is easy to use due to the devices being unity-gain stable, including a RFI and EMI filter, and being free from phase reversal in an overdrive condition.

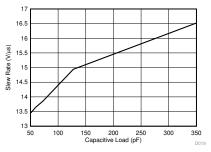
Device information								
PART NUMBER	PACKAGE	BODY SIZE (NOM)						
	SOT-23 (5)	1.60 mm × 2.90 mm						
TLV9051	SC70 (5)	1.25 mm × 2.00 mm						
12/9051	SOT553 (5) ⁽²⁾	1.65 mm × 1.20 mm						
	X2SON (5)	0.80 mm × 0.80 mm						
TLV9051S	SOT-23 (6)	1.60 mm × 2.90 mm						
	SOIC (8)	3.91 mm × 4.90 mm						
	TSSOP (8)	3.00 mm × 4.40 mm						
TLV9052	VSSOP (8)	3.00 mm × 3.00 mm						
	SOT-23 (8)	1.60 mm × 2.90 mm						
	WSON (8)	2.00 mm × 2.00 mm						
	VSSOP (10)	3.00 mm × 3.00 mm						
TLV9052S	X2QFN (10)	1.50 mm × 2.00 mm						
	SOIC (14)	8.65 mm × 3.91 mm						
TL 10054	TSSOP (14)	4.40 mm × 5.00 mm						
TLV9054	X2QFN (14)	2.00 mm × 2.00 mm						
	WQFN (16)	3.00 mm × 3.00 mm						
TLV9054S	WQFN (16)	3.00 mm × 3.00 mm						
(4) F an all available								

Device Information⁽¹⁾

 For all available packages, see the orderable addendum at the end of the data sheet.

(2) Package is for preview only.

Slew Rate vs Load Capacitance





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Table of Contents

1	Feat	tures 1									
2	Applications 1										
3	Description 1										
4	Rev	ision History 2									
5	Dev	ice Comparison Table 4									
6	Pin	Configuration and Functions 5									
7	Spe	cifications12									
	7.1	Absolute Maximum Ratings 12									
	7.2	ESD Ratings 12									
	7.3	Recommended Operating Conditions 12									
	7.4	Thermal Information for Single Channel 12									
	7.5	Thermal Information for Dual Channel 13									
	7.6	Thermal Information for Quad Channel 13									
	7.7	Electrical Characteristics: V _S (Total Supply Voltage) = $(V+) - (V-) = 1.8 V$ to 5.5 V									
	7.8	Typical Characteristics 16									
8	Deta	ailed Description 23									
	8.1	Overview 23									
	8.2	Functional Block Diagram 23									

	8.3	Feature Description	24
	8.4	Device Functional Modes	
9	App	lication and Implementation	
	9.1	Application Information	28
	9.2	Typical Low-Side Current Sense Application	
10	Pow	ver Supply Recommendations	30
11		out	
		Layout Guidelines	
		Layout Example	
12		ice and Documentation Support	
	12.1	Documentation Support	33
	12.2	Related Links	33
	12.3	Receiving Notification of Documentation Updates	33
	12.4	Community Resources	33
	12.5	Trademarks	33
	12.6	Electrostatic Discharge Caution	33
	12.7	Glossary	33
13	Мес	hanical, Packaging, and Orderable	
	Info	mation	34

4 Revision History

2

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision G (September 2019) to Revision H					
•	Added new human-body model and charged-device model ratings for TLV9051 X2SON package to the ESD Rating	ys 12			

Changes from Revision F (June 2019) to Revision G

•	Deleted preview tags for all TLV9051 packages 1
•	Deleted preview tags for the TLV9052 SOT-23 (8) - DDF package
•	Added link to Shutdown Function section in all of the SHDN pin function rows
•	Added EMI Rejection section to Feature Description section
•	Added clarification to the Shutdown Function section

Changes from Revision E (May 2019) to Revision F

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•	Deleted package preview notation for TLV9052S devices in <i>Device Information</i>
•	Deleted package preview notation for TLV9052S devices under Device Comparison Table
•	Deleted preview notation for TLV9052S devices in Device Comparison Table 4
•	Deleted package preview notation for TLV9052S in Pin Configuration and Functions section
•	Deleted package preview notation for TLV9052S under Thermal Information for Dual Channel

Cł	hanges from Revision D (April 2019) to Revision E	Page
•	Added DDF (SOT-23) information to Thermal Information for Dual Channel table	13

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Page

Page

Changes from Original (August 2018) to Revision A

TLV9051, TLV9052, TLV9054

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С	hanges from Revision C (April 2019) to Revision D	Page
•	Deleted preview notations for TLV9054/S devices in Device Information	1
•	Deleted preview notations for TLV9054 devices in Device Comparison Table	4
•	Deleted preview notations for TLV9054S device in Device Comparison Table	4
•	Deleted preview notations for TLV9054 packages in Pin Configurations and Functions section	9
•	Deleted preview notation for TLV9054S RTE package in Pin Configurations and Functions section	11
•	Deleted preview notation for TLV9054/S packages in Thermal Information for Quad Channel	13

Changes from Revision B (March 2019) to Revision C

• A	Added TLV9051 thermal information for DPW, DBV, and DCK packages	12
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Changes from Revision A (December 2018) to Revision B

•	Added Shutdown device notes in the Description section	1
•	Added SOT-23 (8) package to Device Information	1
•	Added Shutdown devices to Device Information	1
•	Added X2QFN (RUC) package to TLV9054 Device Information	1
•	Added DDF package information to Device Comparison Table	. 4
•	Added Shutdown devices (TLV9051S/TLV9052S/TLV9054S) and packages (DGS/RUG/RTE) to Device Comparison Table	
•	Added TLV9051S pinout information to Pin Configurations and Functions section	
•	Added DDF (SOT-23) package	7
•	Added TLV9052S pinout information to Pin Configurations and Functions section	8
•	Added TLV9054S and TLV9054 X2QFN (RUC) pinout information to Pin Configurations and Functions section	9
•	Added TLV9051 and TLV9051S thermal information to Thermal Information for Single Channel	12
•	Added TLV9052S thermal info to Thermal Information for Dual Channel	13
•	Added DDF (SOT-23) package to Thermal Information for Dual Channel	13
•	Added TLV9054 and TLV9054S thermal information to Thermal Information for Quad Channel	13
•	Added Shutdown Function information in Feature Description section	26
•	Added "S" suffix to Related Links to reflect the addition of Shutdown devices	



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Page

Page

Page

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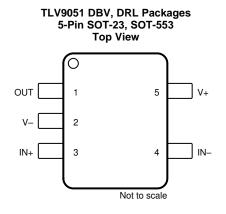
5 Device Comparison Table

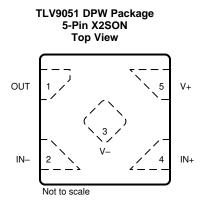
PACKAGE LEADS														
DEVICE	NO. OF CH.	SC70 DCK	SOT-23 DBV	SOT- 553 <mark>(1)</mark> DRL	X2SON DPW	SOIC D	WSON DSG	VSSOP DGK	TSSOP PW	SOT-23 DDF	VSSOP DGS	X2QFN RUG	X2QFN RUC	WQFN RTE
TLV9051	1	5	5	5	5	_	_	—	—	_	_	_	—	_
TLV9051S		_	6	—	_	_	_	—	_	_	_	_	_	_
TLV9052	2	_	—	—	_	8	8	8	8	8	_	_	_	_
TLV9052S	2	_	—	—	_	_	_	—	_	_	10	10	_	_
TLV9054	4	_	_	_	_	14	_	_	14	_	_	_	14	16
TLV9054S	4	_	—	—	—	_	—	—	—	_	—	—	—	16

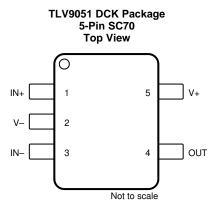
(1) Package is for preview only.



6 Pin Configuration and Functions



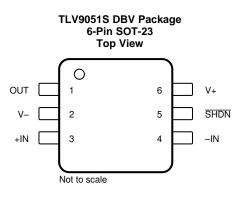




Pin Functions: TLV9051

		PIN			
NAME	SOT-23, SOT-553	SC-70	X2SON	I/O	DESCRIPTION
IN-	4	3	2	I	Inverting input
IN+	3	1	4	I	Noninverting input
OUT	1	4	1	0	Output
V–	2	2	3	—	Negative (low) supply or ground (for single-supply operation)
V+	5	5	5	_	Positive (high) supply



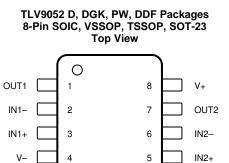


Pin Functions: TLV9051S

PIN		1/0	DESCRIPTION			
NAME	NO.	I/O	DESCRIPTION			
-IN	4	I	Inverting input			
+IN	3	I	Noninverting input			
OUT	1	0	Output			
SHDN	5	I	Shutdown: low = amp disabled, high = amp enabled. See <i>Shutdown Function</i> section for more information.			
V–	2	_	Negative (lowest) supply or ground (for single-supply operation).			
V+	6	_	Positive (highest) supply			

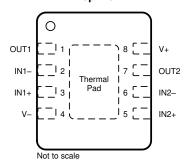
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Not to scale

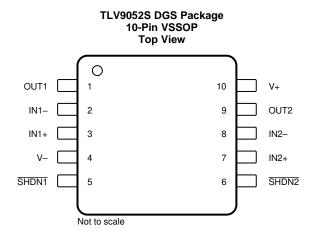
TLV9052 DSG Package 8-Pin WSON With Exposed Thermal Pad Top View

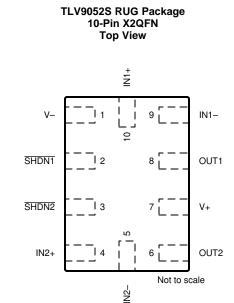


Connect exposed thermal pad to V–. See *Packages With an Exposed Thermal Pad* section for more information.

Pin Functions: TLV9052

	PIN	1/0	DESCRIPTION			
NAME	NO.	1/0	DESCRIPTION			
IN1-	2	Ι	Inverting input, channel 1			
IN1+	3	Ι	Noninverting input, channel 1			
IN2-	6	Ι	iverting input, channel 2			
IN2+	5	Ι	Noninverting input, channel 2			
OUT1	1	0	Output, channel 1			
OUT2	7	0	Output, channel 2			
V–	4	_	Negative (low) supply or ground (for single-supply operation)			
V+	8	_	Positive (high) supply			



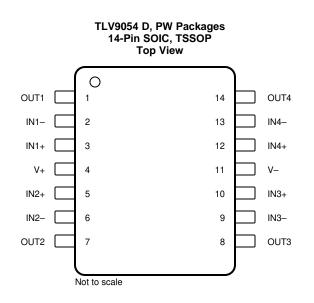


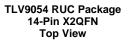
Pin Functions: TLV9052S

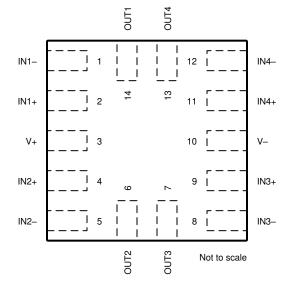
	PIN		1/0	DESCRIPTION
NAME	VSSOP	X2QFN	I/O	DESCRIPTION
IN1-	2	9	Ι	Inverting input, channel 1
IN1+	3	10	I	Noninverting input, channel 1
IN2-	8	5	I	Inverting input, channel 2
IN2+	7	4	Ι	Noninverting input, channel 2
OUT1	1	8	0	Output, channel 1
OUT2	9	6	0	Output, channel 2
SHDN1	5	2	I	Shutdown: low = amp disabled, high = amp enabled, channel 1. See <i>Shutdown Function</i> section for more information.
SHDN2	6	3	I	Shutdown: low = amp disabled, high = amp enabled, channel 2. See <i>Shutdown Function</i> section for more information.
V–	4	1	_	Negative (low) supply or ground (for single-supply operation)
V+	10	7		Positive (high) supply

8

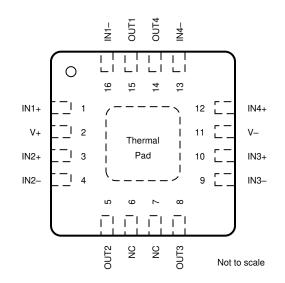












Connect exposed thermal pad to V–. See *Packages With an Exposed Thermal Pad* section for more information.

P	IN						
SOIC, TSSOP	WQFN	X2QFN	I/O	DESCRIPTION			
2	16	1	Ι	Inverting input, channel 1			
3	1	2	I	Noninverting input, channel 1			
6	4	5	I	Inverting input, channel 2			
5	3	4	I	Noninverting input, channel 2			
9	9	8	I	Inverting input, channel 3			
10	10	9	I	Noninverting input, channel 3			
13	13	12	I	Inverting input, channel 4			
12	12	11	I	Noninverting input, channel 4			
	SOIC, TSSOP 2 3 6 5 9 10 13	TSSOP WQFN 2 16 3 1 6 4 5 3 9 9 10 10 13 13	SOIC, TSSOP WQFN X2QFN 2 16 1 3 1 2 6 4 5 5 3 4 9 9 8 10 10 9 13 13 12	SOIC, TSSOP WQFN X2QFN I/O 2 16 1 1 3 1 2 1 6 4 5 1 5 3 4 1 9 9 8 1 10 10 9 1 13 13 12 1			

Pin Functions: TLV9054

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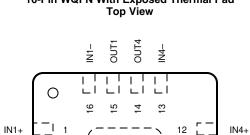
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	PIN				
NAME	SOIC, TSSOP	WQFN	X2QFN	I/O	DESCRIPTION
NC	—	6, 7	—	—	No internal connection
OUT1	1	15	14	0	Output, channel 1
OUT2	7	5	6	0	Output, channel 2
OUT3	8	8	7	0	Output, channel 3
OUT4	14	14	13	0	Output, channel 4
V–	11	11	10	—	Negative (low) supply or ground (for single-supply operation)
V+	4	2	3	_	Positive (high) supply

Pin Functions: TLV9054 (continued)





Thermal

Pad

V–

IN3+

IN3-

Not to scale

11

10

9

1

1

OUT3 SHDN34

V+

IN2+

IN2-

2

3

4

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> OUT2 SHDN12

TLV9054S RTE Package 16-Pin WQFN With Exposed Thermal Pad Top View

Connect exposed thermal pad to V-. See Packages With an Exposed Thermal Pad section for more information.

1_1

Pin Functions: TLV9054S

PIN I/O			DECODIDITION
NAME	NO.	1/0	DESCRIPTION
IN1+	1	I	Noninverting input, channel 1
IN1-	16	I	Inverting input, channel 1
IN2+	3	I	Noninverting input, channel 2
IN2-	4	I	Inverting input, channel 2
IN3+	10	I	Noninverting input, channel 3
IN3–	9	I	Inverting input, channel 3
IN4+	12	I	Noninverting input, channel 4
IN4–	13	I	Inverting input, channel 4
SHDN12	6	I	Shutdown: low = amp disabled, high = amp enabled, channel 1 and 2. See <i>Shutdown Function</i> section for more information.
SHDN34	7	I	Shutdown: low = amp disabled, high = amp enabled, channel 3 and 4. See <i>Shutdown Function</i> section for more information.
OUT1	15	0	Output, channel 1
OUT2	5	0	Output, channel 2
OUT3	8	0	Output, channel 3
OUT4	14	0	Output, channel 4
V–	11	_	Negative (low) supply or ground (for single-supply operation)
V+	2	_	Positive (high) supply

7 Specifications

7.1 Absolute Maximum Ratings

over operating junction temperature (unless otherwise noted)⁽¹⁾

			MIN	MAX	UNIT
Supply voltage, V_S	= (V+) - (V-)			6	V
Signal input pins	Voltage ⁽²⁾	Common-mode	(V–) – 0.5	(V+) + 0.5	V
	voltage -/	Differential		V _S + 0.2	V
	Current ⁽²⁾		-10	10	0.5 V
Output short-circuit	(3)		Contir	nuous	
Operating ambient	temperature, T _A		-40	150	°C
Junction temperature, T _J				150	°C
Storage temperatur	e, T _{stg}		-65	150	°C

(1) Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) Input pins are diode-clamped to the power-supply rails. Current limit input signals that can swing more than 0.5 V beyond the supply rails to 10 mA or less.

(3) Short-circuit to ground, one amplifier per package.

7.2 ESD Ratings

			VALUE	UNIT					
TLV905	51 X2SON PACKAGE								
V	V _(ESD) Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±3000	V					
V(ESD)		Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±1500						
ALL OT	ALL OTHER PACKAGES								
V	Electrostatio discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±4000	V					
V _(ESD)	Electrostatic discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±1500	V					

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

7.3 Recommended Operating Conditions

over operating junction temperature range (unless otherwise noted)

		MIN	MAX	UNIT
Vs	Supply voltage, $V_S = (V+) - (V-)$	1.8	5.5	V
V _{IN}	Input pin voltage	(V–) – 0.1	(V+) + 0.1	V
	Specified temperature	-40	125	°C

7.4 Thermal Information for Single Channel

		TLV9051, TLV9051S						
	THERMAL METRIC ⁽¹⁾	DPW (X2SON) DBV (S		SOT-23)	DCK (SC70)	DRL (SOT553) ⁽²⁾	UNIT	
		5 PINS	5 PINS	6 PINS	5 PINS	5 PINS		
R_{\thetaJA}	Junction-to-ambient thermal resistance	470.0	228.1	210.8	231.2	TBD	°C/W	
$R_{\theta JC(top)}$	Junction-to-case(top) thermal resistance	211.9	152.1	152.1	144.4	TBD	°C/W	
$R_{\theta JB}$	Junction-to-board thermal resistance	334.8	97.7	92.3	78.6	TBD	°C/W	
ΨJT	Junction-to-top characterization parameter	29.8	74.1	76.2	51.3	TBD	°C/W	

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report.

- (2) This package option is for preview only.
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Thermal Information for Single Channel (continued)

		TLV9051, TLV9051S					
THERMAL METRIC ⁽¹⁾		DPW (X2SON) DBV (SC		SOT-23)	DCK (SC70)	DRL (SOT553) ⁽²⁾	UNIT
		5 PINS	5 PINS	6 PINS	5 PINS	5 PINS	
ΨЈВ	Junction-to-board characterization parameter	333.2	97.3	92.1	78.3	TBD	°C/W
$R_{\theta JC(bot)}$	Junction-to-case(bottom) thermal resistance	N/A	N/A	N/A	N/A	TBD	°C/W

7.5 Thermal Information for Dual Channel

		TLV9052, TLV9052S							
т	THERMAL METRIC ⁽¹⁾		DGK (VSSOP)	DSG (WSON)	PW (TSSOP)	DDF (SOT-23)	DGS (VSSOP)	RUG (X2QFN)	UNIT
		8 PINS	8 PINS	8 PINS	8 PINS	8 PINS	10 PINS	10 PINS	
R_{\thetaJA}	Junction-to-ambient thermal resistance	155.4	208.8	102.3	205.1	184.4	170.4	197.2	°C/W
$R_{\theta JC(top)}$	Junction-to-case(top) thermal resistance	95.5	93.3	120.0	93.7	112.8	84.9	93.3	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	98.9	130.7	68.2	135.7	99.9	113.5	123.8	°C/W
ΨJT	Junction-to-top characterization parameter	41.9	26.1	15.1	25.0	18.7	16.4	3.7	°C/W
ΨЈВ	Junction-to-board characterization parameter	98.1	128.9	68.2	134.0	99.3	112.3	120.2	°C/W
R _{0JC(bot)}	Junction-to-case(bottom) thermal resistance	N/A	N/A	43.6	N/A	N/A	N/A	N/A	°C/W

(1) For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

7.6 Thermal Information for Quad Channel

		TLV9054, TLV9054S						
	THERMAL METRIC ⁽¹⁾	D (SOIC)	PW (TSSOP)	RTE (WQFN)		RUC (X2SQFN)	UNIT	
		14 PINS	14 PINS 14 PINS		16 PINS	14 PINS		
R_{\thetaJA}	Junction-to-ambient thermal resistance	115.0	147.2	65.5	65.6	209.4	°C/W	
$R_{\theta JC(top)}$	Junction-to-case(top) thermal resistance	71.1	67.2	70.6	70.6	68.8	°C/W	
$R_{\theta JB}$	Junction-to-board thermal resistance	71.0	91.6	40.5	40.5	153.3	°C/W	
тιΨ	Junction-to-top characterization parameter	29.7	16.6	5.8	5.8	3.0	°C/W	
ΨJB	Junction-to-board characterization parameter	70.6	90.7	40.5	40.5	152.8	°C/W	
$R_{\theta JC(bot)}$	Junction-to-case(bottom) thermal resistance	N/A	N/A	24.5	24.5	N/A	°C/W	

(1) For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.



7.7 Electrical Characteristics: V_s (Total Supply Voltage) = (V+) – (V–) = 1.8 V to 5.5 V

For V_S = (V+) – (V–) = 1.8 V to 5.5 V (±0.9 V to ±2.75 V) at T_A = 25°C, R_L = 10 k Ω connected to V_S / 2, V_{CM} = V_S / 2, and V_{OUT} = V_S / 2 (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
OFFSET	VOLTAGE	·					
.,		V _S = 5 V		±0.33	±1.6		
V _{OS}	Input offset voltage	$V_{\rm S} = 5 \rm V$			±2	mV	
dV _{OS} /dT	Drift	V _S = 5 V	$T_A = -40^{\circ}C$ to $125^{\circ}C$		±0.5		µV/°C
PSRR	Power-supply rejection ratio	$V_{S} = 1.8 \text{ V} - 5.5 \text{ V}, V_{CM} = (V-)$		±13	±80	μV/V	
	Channel separation, DC	At DC			100		dB
INPUT BI	AS CURRENT						
I _B	Input bias current				±2		pА
I _{OS}	Input offset current				±1		pА
NOISE							
En	Input voltage noise (peak- to-peak)	$V_{S} = 5 V, f = 0.1 Hz \text{ to } 10 Hz$			6		μV_{PP}
0	Input voltage noise density	V _S = 5 V, f = 10 kHz			15		nV/√Hz
e _n	mput voltage noise density	$V_S = 5 V$, f = 1 kHz		20		11 V / VE12	
i _n	Input current noise density	f = 1 kHz			18		fA/√Hz
	OLTAGE RANGE						
V _{CM}	Common-mode voltage range	V _S = 1.8 V to 5.5 V		(V–) – 0.1		(V+) + 0.1	V
		$V_{S} = 5.5 \text{ V}, (V-) - 0.1 \text{ V} < V_{CM} < (V+) - 1.4 \text{ V}$	$T_A = -40^{\circ}C$ to $125^{\circ}C$	80	96		
CMRR	Common-mode rejection	V_{S} = 5.5 V, V_{CM} = –0.1 V to 5.6 V	$T_A = -40^{\circ}C$ to $125^{\circ}C$	62	79		dB
OWINK	ratio	$V_{S} = 1.8 \text{ V}, (V-) - 0.1 \text{ V} < V_{CM} < (V+) - 1.4 \text{ V}$	$T_A = -40^{\circ}C$ to $125^{\circ}C$		88		UD
		V_{S} = 1.8 V, V_{CM} = –0.1 V to 1.9 V	$T_A = -40^{\circ}C$ to $125^{\circ}C$		72		
	APACITANCE						
C _{ID}	Differential				2		pF
C _{IC}	Common-mode				4		pF
OPEN-LC	OOP GAIN						
		$V_{S} = 1.8 \text{ V}, (V-) + 0.04 \text{ V} < V_{O} < (V+) - 0.04 \text{ V}$, $R_L = 10 \text{ k}\Omega$		106		
٨		$V_{S} = 5.5 \text{ V}, (V-) + 0.05 \text{ V} < V_{O} < (V+) - 0.05 \text{ V}$	104	128		dB	
A _{OL}	Open-loop voltage gain	$V_{\rm S}$ = 1.8 V, (V–) + 0.06 V < V _O < (V+) – 0.06 V		108		uв	
		$V_{S} = 5.5 \text{ V}, (V-) + 0.15 \text{ V} < V_{O} < (V+) - 0.15 \text{ V}$		130			
FREQUE	NCY RESPONSE						
GBW	Gain bandwidth product	V _S = 5.5 V, G = +1			5		MHz
φm	Phase margin	V _S = 5.5 V, G = +1			60		0
SR	Slew rate	$V_{S} = 5.5 \text{ V}, \text{ G} = +1, \text{ C}_{L} = 130 \text{ pF}$			15		V/µs
	Sottling time	To 0.1%, V _S = 5.5 V, 2-V step , G = +1, C _L = 1		0.75			
t _S	Settling time	To 0.01%, $V_S = 5.5 V$, 2-V step, G = +1, $C_L = 1$	= 5.5 V, 2-V step, G = +1, C _L = 100 pF				μs
t _{OR}	Overload recovery time	$V_{S} = 5 V, V_{IN} \times gain > V_{S}$		0.3		μs	
THD + N	Total harmonic distortion + noise ⁽¹⁾	$V_{S} = 5.5 \text{ V}, V_{CM} = 2.5 \text{ V}, V_{O} = 1 \text{ V}_{RMS}, \text{ G} = +1,$	f = 1 kHz		0.0006%		

(1) Third-order filter; bandwidth = 80 kHz at -3 dB.



Electrical Characteristics: V_s (Total Supply Voltage) = (V+) – (V–) = 1.8 V to 5.5 V (continued)

For $V_S = (V+) - (V-) = 1.8$ V to 5.5 V (±0.9 V to ±2.75 V) at $T_A = 25^{\circ}$ C, $R_L = 10$ k Ω connected to $V_S / 2$, $V_{CM} = V_S / 2$, and $V_{OUT} = V_S / 2$ (unless otherwise noted)

	PARAMETER	TEST CONDITIO	NS	MIN	TYP	MAX	UNIT	
OUTPU	т							
			$R_L = 2 k\Omega$			40		
Vo	Voltage output swing from	Positive rail headroom, $V_S = 5.5 V$	$R_L = 10 \text{ k}\Omega$			16	mV	
	rail		$R_L = 2 k\Omega$			40	mv	
		Negative rail headroom, $V_S = 5.5 V$	$R_L = 10 \ k\Omega$			16	I	
I _{SC}	Short-circuit current	$V_{S} = 5 V$			±50		mA	
Z _O	Open-loop output impedance	V _S = 5 V, f = 5 MHz		250		Ω		
POWER	R SUPPLY							
	Quiescent current per	$V_{\rm S} = 5.5 \text{ V}, \text{ I}_{\rm O} = 0 \text{ mA}$		330	450	μA		
Ι _Q	amplifier	$V_{\rm S} = 5.5 \text{ V}, I_{\rm O} = 0 \text{ mA}$	$T_A = -40^{\circ}C$ to $125^{\circ}C$		475	μΑ		
SHUTD	OWN							
I _{QSD}	Quiescent current per amplifier	$V_{\rm S}$ = 1.8 V to 5.5 V, all amplifiers disabled,	$\rm V_S$ = 1.8 V to 5.5 V, all amplifiers disabled, $\overline{\rm SHDN}$ = $\rm V_S-$					
Z _{SHDN}	Output impedance during shutdown	V_{S} = 1.8 V to 5.5 V, amplifier disabled		10 8		GΩ∥ pF		
V _{IH}	High voltage (amplifier enabled)	V_{S} = 1.8 V to 5.5 V, amplifier enabled		(V–) + 0.9	(V–) + 1.1	V		
V _{IL}	Low voltage (amplifier disabled)	V_{S} = 1.8 V to 5.5 V, amplifier disabled	(V–) + 0.2	(V–) + 0.7		V		
	Amplifier enable time (full shutdown) ⁽²⁾⁽³⁾	V_{S} = 1.8 V to 5.5 V, full shutdown; G = 1, V		35				
t _{ON}	Amplifier enable time (partial shutdown) ⁽²⁾⁽³⁾	V_{S} = 1.8 V to 5.5 V, partial shutdown; G = $\frac{1}{2}$		10		μs		
t _{OFF}	Amplifier disable time ⁽²⁾	$V_{\rm S}$ = 1.8 V to 5.5 V, G = 1, $V_{\rm OUT}$ = 0.1 × $V_{\rm S}$	/ 2		6		μs	
	SHDN pin input bias	$V_{S} = 1.8 \text{ V to } 5.5 \text{ V}, \text{ V+} \ge \overline{\text{SHDN}} \ge (\text{V+}) - 0$		40		-		
	current (per pin)	$V_{\rm S} = 1.8$ V to 5.5 V, V- $\leq \overline{\rm SHDN} \leq (V-) + 0$	160			nA		

(2) Disable time (t_{OFF}) and enable time (t_{ON}) are defined as the time interval between the 50% point of the signal applied to the SHDN pin and the point at which the output voltage reaches the 10% (disable) or 90% (enable) level.

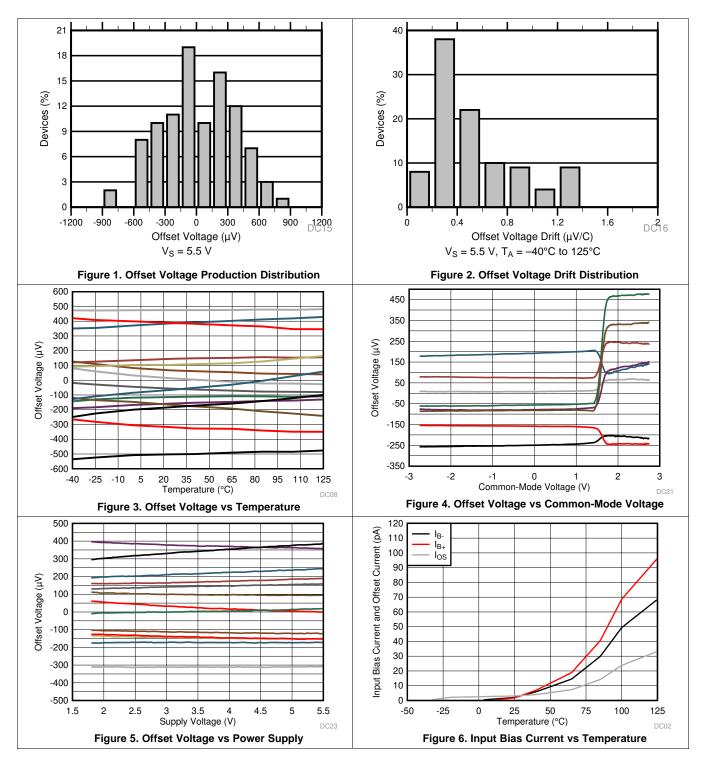
(3) Full shutdown refers to the dual TL/9052S having both channels 1 and 2 disabled (SHDN_1 = SHDN_2 = V_) and the quad TL/9054S having all channels 1 to 4disabled (SHDN_12 = SHDN_34 = V_-). For partial shutdown, only one SHDN pin is exercised; in this mode, the internal biasing circuitry remains operational and the enable time is shorter.

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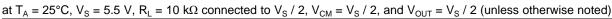
7.8 Typical Characteristics

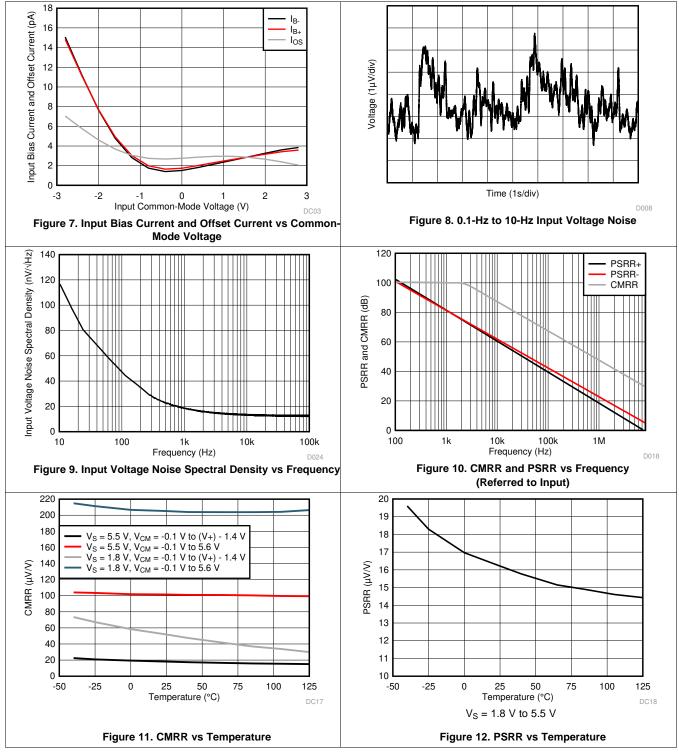
at $T_A = 25^{\circ}C$, $V_S = 5.5$ V, $R_L = 10$ k Ω connected to V_S / 2, $V_{CM} = V_S$ / 2, and $V_{OUT} = V_S$ / 2 (unless otherwise noted)





Typical Characteristics (continued)



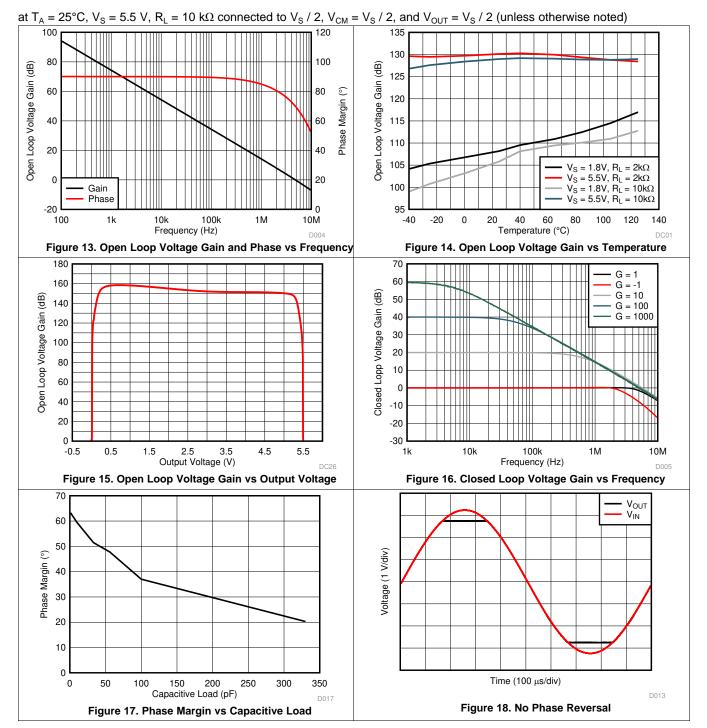


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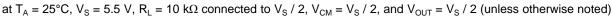
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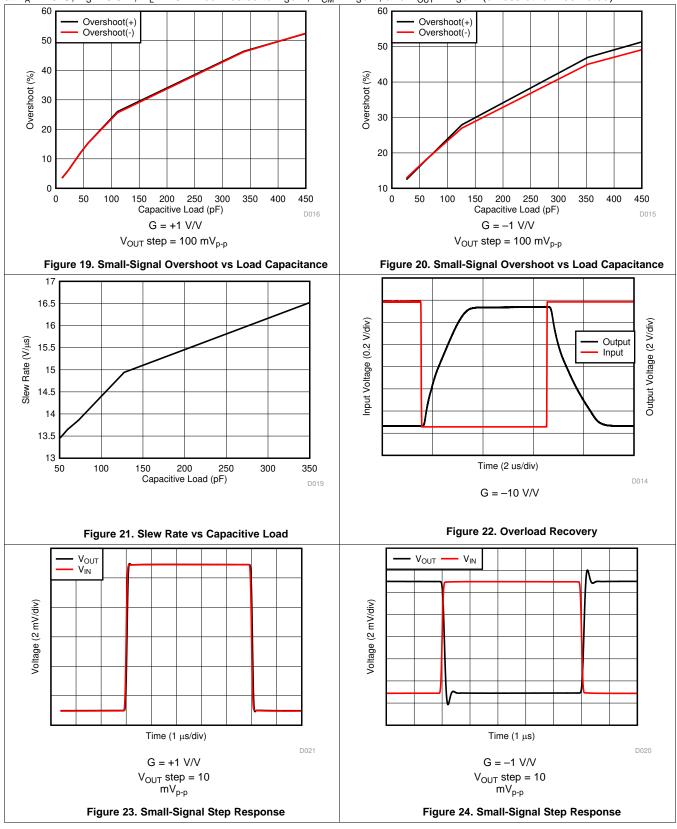
Typical Characteristics (continued)





Typical Characteristics (continued)

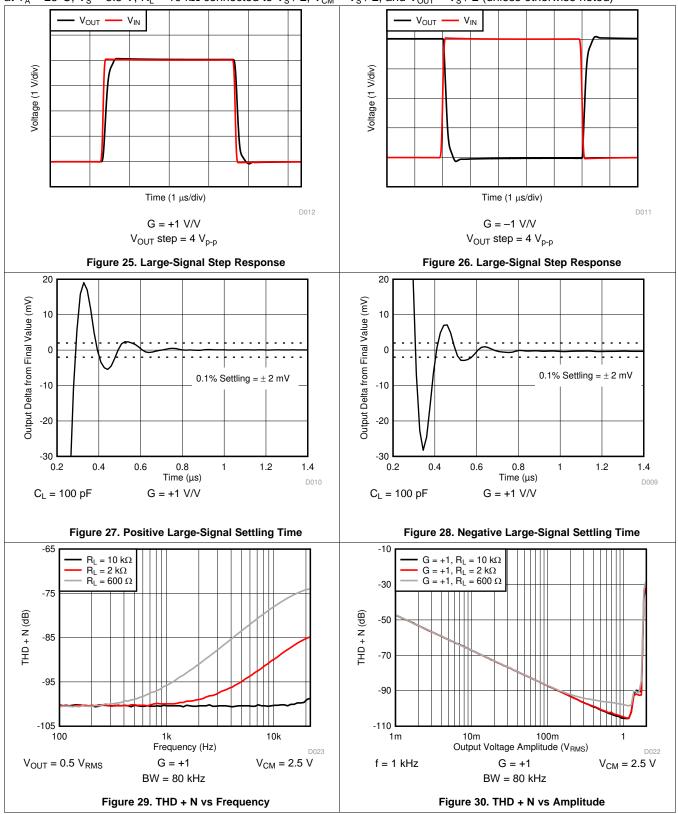




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Typical Characteristics (continued)

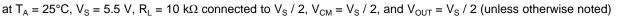
at $T_A = 25^{\circ}$ C, $V_S = 5.5$ V, $R_L = 10$ k Ω connected to V_S / 2, $V_{CM} = V_S$ / 2, and $V_{OUT} = V_S$ / 2 (unless otherwise noted)

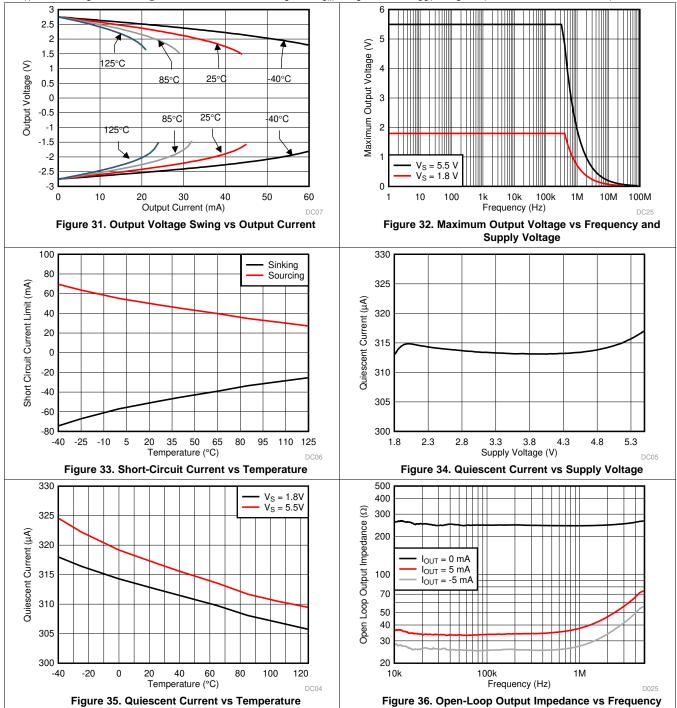


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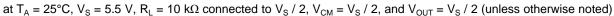


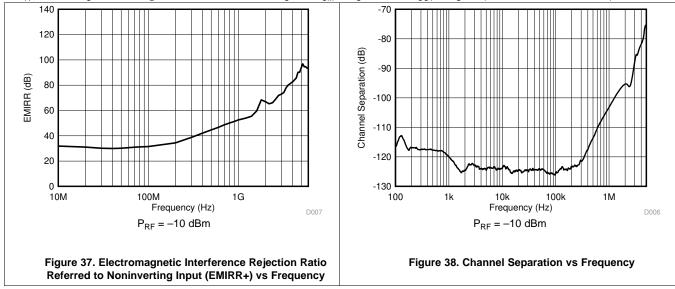
Typical Characteristics (continued)





Typical Characteristics (continued)





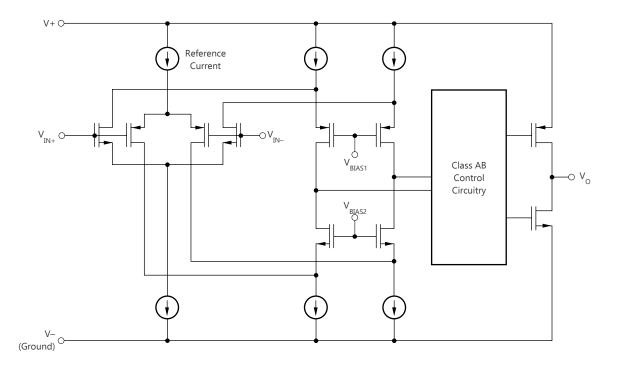


8 Detailed Description

8.1 Overview

The TLV905x devices are a 5-MHz family of low-power, rail-to-rail input and output op amps. These devices operate from 1.8 V to 5.5 V, are unity-gain stable, and are designed for a wide range of general-purpose applications. The input common-mode voltage range includes both rails and allows the TLV905x family to be used in virtually any single-supply application. The unique combination of a high slew rate and low quiescent current makes this family a potential choice for battery-powered motor-drive applications. Rail-to-rail input and output swing significantly increase dynamic range, especially in low-supply applications.

8.2 Functional Block Diagram





8.3 Feature Description

8.3.1 Operating Voltage

The TLV905x family of op amps is specified for operation from 1.8 V to 5.5 V. In addition, many specifications apply from -40°C to 125°C. Parameters that vary significantly with operating voltages or temperature are illustrated in the *Typical Characteristics* section.

8.3.2 Rail-to-Rail Input

The input common-mode voltage range of the TLV905x family extends 100 mV beyond the supply rails for the full supply voltage range of 1.8 V to 5.5 V. This performance is achieved with a complementary input stage: an N-channel input differential pair in parallel with a P-channel differential pair, as shown in the *Functional Block Diagram*. The N-channel pair is active for input voltages close to the positive rail, typically (V+) - 1.4 V to 200 mV above the positive supply, whereas the P-channel pair is active for inputs from 200 mV below the negative supply to approximately (V+) - 1.4 V. There is a small transition region, typically (V+) - 1.2 V to (V+) - 1 V, in which both pairs are on. This 200-mV transition region can vary up to 200 mV with process variation. Thus, the transition region (with both stages on) can range from (V+) - 1.4 V to (V+) - 1.2 V on the low end, and up to (V+) - 1 V to (V+) - 0.8 V on the high end. Within this transition region, PSRR, CMRR, offset voltage, offset drift, and THD can degrade compared to device operation outside this region.

8.3.3 Rail-to-Rail Output

Designed as low-power, low-voltage operational amplifiers, the TLV905x family delivers a robust output drive capability. A class AB output stage with common-source transistors achieves full rail-to-rail output swing capability. For resistive loads of 10 k Ω , the output swings to within 16 mV of either supply rail, regardless of the applied power-supply voltage. Different load conditions change the ability of the amplifier to swing close to the rails.

8.3.4 EMI Rejection

The TLV905x uses integrated electromagnetic interference (EMI) filtering to reduce the effects of EMI from sources such as wireless communications and densely-populated boards with a mix of analog signal chain and digital components. EMI immunity can be improved with circuit design techniques; the TLV905x benefits from these design improvements. Texas Instruments has developed the ability to accurately measure and quantify the immunity of an operational amplifier over a broad frequency spectrum extending from 10 MHz to 6 GHz. Figure 39 shows the results of this testing on the TLV905x. Table 1 shows the EMIRR IN+ values for the TLV905x at particular frequencies commonly encountered in real-world applications. The *EMI Rejection Ratio of Operational Amplifiers* application report contains detailed information on the topic of EMIRR performance as it relates to op amps and is available for download from www.ti.com.

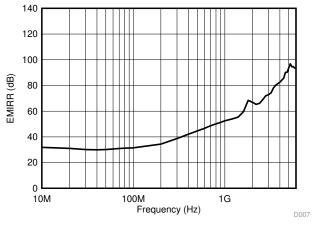


Figure 39. EMIRR Testing



Feature Description (continued)

Table 1. TLV905x EMIRR IN+ for Frequencies of Interest

FREQUENCY	APPLICATION OR ALLOCATION	EMIRR IN+
400 MHz	Mobile radio, mobile satellite, space operation, weather, radar, ultra-high frequency (UHF) applications	59.5 dB
900 MHz	Global system for mobile communications (GSM) applications, radio communication, navigation, GPS (to 1.6 GHz), GSM, aeronautical mobile, UHF applications	68.9 dB
1.8 GHz	GSM applications, mobile personal communications, broadband, satellite, L-band (1 GHz to 2 GHz)	77.8 dB
2.4 GHz	802.11b, 802.11g, 802.11n, Bluetooth [®] , mobile personal communications, industrial, scientific and medical (ISM) radio band, amateur radio and satellite, S-band (2 GHz to 4 GHz)	78.0 dB
3.6 GHz	Radiolocation, aero communication and navigation, satellite, mobile, S-band	88.8 dB
5 GHz	802.11a, 802.11n, aero communication and navigation, mobile communication, space and satellite operation, C-band (4 GHz to 8 GHz)	87.6 dB

8.3.5 Overload Recovery

Overload recovery is defined as the time required for the operational amplifier output to recover from a saturated state to a linear state. The output devices of the operational amplifier enter a saturation region when the output voltage exceeds the rated operating voltage, because of the high input voltage or high gain. After the device enters the saturation region, the output devices require time to return to the linear operating state. After the output devices return to their linear operating state, the device begins to slew at the specified slew rate. Therefore, the propagation delay (in case of an overload condition) is the sum of the overload recovery time and the slew time. The overload recovery time for the TLV905x family is approximately 300 ns.

8.3.6 Packages With an Exposed Thermal Pad

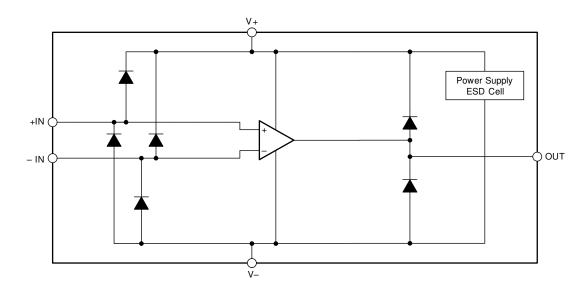
The TLV905x family is available in packages such as the WSON-8 (DSG) and WQFN-16 (RTE) which feature an exposed thermal pad. Inside the package, the die is attached to this thermal pad using an electrically conductive compound. For this reason, when using a package with an exposed thermal pad, the thermal pad must either be connected to V– or left floating. Attaching the thermal pad to a potential other then V– is not allowed, and the performance of the device is not assured when doing so.

8.3.7 Electrical Overstress

Designers often ask questions about the capability of an operational amplifier to withstand electrical overstress. These questions tend to focus on the device inputs, but can involve the supply voltage pins or even the output pin. Each of these different pin functions have electrical stress limits determined by the voltage breakdown characteristics of the particular semiconductor fabrication process and specific circuits connected to the pin. Additionally, internal electrostatic discharge (ESD) protection is built into these circuits to protect them from accidental ESD events both before and during product assembly.

Having a good understanding of this basic ESD circuitry and its relevance to an electrical overstress event is helpful. Figure 40 shows the ESD circuits contained in the TLV905x devices. The ESD protection circuitry involves several current-steering diodes connected from the input and output pins and routed back to the internal power supply lines, where they meet at an absorption device internal to the operational amplifier. This protection circuitry is intended to remain inactive during normal circuit operation.







8.3.8 Input Protection

The TLV905x family incorporates internal ESD protection circuits on all pins. For input and output pins, this protection primarily consists of current-steering diodes connected between the input and power-supply pins. These ESD protection diodes provide in-circuit, input overdrive protection, as long as the current is limited to 10 mA, as shown in the *Absolute Maximum Ratings*. Figure 41 shows how a series input resistor can be added to the driven input to limit the input current. The added resistor contributes thermal noise at the amplifier input and the value must be kept to a minimum in noise-sensitive applications.

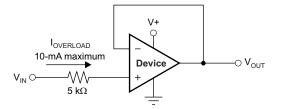


Figure 41. Input Current Protection

8.3.9 Shutdown Function

The TLV905xS devices feature \overline{SHDN} pins that disable the op amp, placing it into a low-power standby mode. In this mode, the op amp typically consumes less than 1 μ A. The \overline{SHDN} pins are active low, meaning that shutdown mode is enabled when the input to the \overline{SHDN} pin is a valid logic low.

The SHDN pins are referenced to the negative supply voltage of the op amp. The threshold of the shutdown feature lies around 800 mV (typical) and does not change with respect to the supply voltage. Hysteresis has been included in the switching threshold to ensure smooth switching characteristics. To ensure optimal shutdown behavior, the SHDN pins should be driven with valid logic signals. A valid logic low is defined as a voltage between V- and V- + 0.4 V. A valid logic high is defined as a voltage between V- + 1.2 V and V+. The shutdown pin circuitry includes a pull-up resistor, which will inherently pull the voltage of the pin to the positive supply rail if not driven. Thus, to enable the amplifier, the SHDN pins should either be left floating or driven to a valid logic high. To disable the amplifier, the SHDN pins must be driven to a valid logic low .While we highly recommend that the shutdown pin be connected to a valid high or a low voltage or driven, we have included a pull-up resistor connected to VCC. The maximum voltage allowed at the SHDN pins is (V+) + 0.5 V. Exceeding this voltage level will damage the device.



The SHDN pins are high-impedance CMOS inputs. Dual op amp versions are independently controlled and quad op amp versions are controlled in pairs with logic inputs. For battery-operated applications, this feature may be used to greatly reduce the average current and extend battery life. The enable time is 35 μ s for full shutdown of all channels; disable time is 6 μ s. When disabled, the output assumes a high-impedance state. This architecture allows the TLV905xS to be operated as a gated amplifier (or to have the device output multiplexed onto a common analog output bus). Shutdown time (t_{OFF}) depends on loading conditions and increases as load resistance increases. To ensure shutdown (disable) within a specific shutdown time, the specified 10-k Ω load to midsupply (V_S / 2) is required. If using the TLV905xS without a load, the resulting turnoff time is significantly increased.

8.4 Device Functional Modes

The TLV905x family is operational when the power-supply voltage is between 1.8 V (±0.9 V) and 5.5 V (±2.75 V).

The TLV905xS devices feature a shutdown mode and are shutdown when a valid logic low is applied to the shutdown pin.

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9 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

The TLV905x family features 5-MHz bandwidth and very high slew rate of 15 V/µs with only 330 µA of supply current per channel, providing excellent AC performance at very low-power consumption. DC applications are well served with a very low input noise voltage of 15 nV/ \sqrt{Hz} at 10 kHz, low input bias current, and a typical input offset voltage of 0.33 mV.

9.2 Typical Low-Side Current Sense Application

Figure 42 shows the TLV905x configured in a low-side current sensing application.

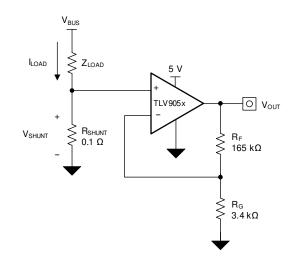


Figure 42. TLV905x in a Low-Side, Current-Sensing Application

9.2.1 Design Requirements

The design requirements for this design are:

- Load current: 0 A to 1 A
- Output voltage: 4.95 V
- Maximum shunt voltage: 100 mV



Typical Low-Side Current Sense Application (continued)

9.2.2 Detailed Design Procedure

The transfer function of the circuit in Figure 42 is given in Equation 1.

$$V_{OUT} = I_{LOAD} \times R_{SHUNT} \times Gain$$

(1)

The load current (I_{LOAD}) produces a voltage drop across the shunt resistor (R_{SHUNT}). The load current is set from 0 A to 1 A. To keep the shunt voltage below 100 mV at maximum load current, the largest shunt resistor is defined using Equation 2.

$$R_{SHUNT} = \frac{V_{SHUNT_MAX}}{I_{LOAD_MAX}} = \frac{100mV}{1A} = 100m\Omega$$
(2)

Using Equation 2, R_{SHUNT} equals 100 m Ω . The voltage drop produced by I_{LOAD} and R_{SHUNT} is amplified by the TLV905x device to produce an output voltage of approximately 0 V to 4.95 V. Equation 3 calculates the gain required for the TLV905x device to produce the required output voltage.

$$Gain = \frac{\left(V_{OUT_MAX} - V_{OUT_MIN}\right)}{\left(V_{IN_MAX} - V_{IN_MIN}\right)}$$
(3)

Using Equation 3, the required gain equals 49.5 V/V, which is set with the R_F and R_G resistors. Equation 4 sizes the R_F and R_G , resistors to set the gain of the TLV905x device to 49.5 V/V.

$$Gain = 1 + \frac{(R_F)}{(R_G)}$$
(4)

Selecting R_F to equal 165 k Ω and R_G to equal 3.4 k Ω provides a combination that equals approximately 49.5 V/V. Figure 43 shows the measured transfer function of the circuit shown in Figure 42.

9.2.3 Application Curve

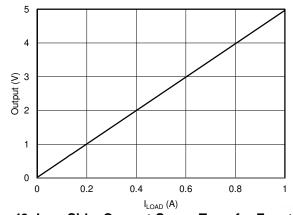


Figure 43. Low-Side, Current-Sense Transfer Function



10 Power Supply Recommendations

The TLV905x family is specified for operation from 1.8 V to 5.5 V (\pm 0.9 V to \pm 2.75 V); many specifications apply from -40° C to 125°C. The *Typical Characteristics* section presents parameters that can exhibit significant variance with regard to operating voltage or temperature.

CAUTION

Supply voltages larger than 6 V can permanently damage the device; see the *Absolute Maximum Ratings* table.

Place 0.1-µF bypass capacitors close to the power-supply pins to reduce errors coupling in from noisy or highimpedance power supplies. For more-detailed information on bypass capacitor placement, see the *Layout Example* section.



11 Layout

11.1 Layout Guidelines

For best operational performance of the device, use good printed circuit board (PCB) layout practices, including:

- Noise can propagate into analog circuitry through the power pins of the circuit as a whole and of the op amp itself. Bypass capacitors are used to reduce the coupled noise by providing low-impedance power sources local to the analog circuitry.
 - Connect low-ESR, 0.1-µF ceramic bypass capacitors between each supply pin and ground, placed as close to the device as possible. A single bypass capacitor from V+ to ground is applicable for singlesupply applications.
- Separate grounding for analog and digital portions of circuitry is one of the simplest and most-effective methods of noise suppression. One or more layers on multilayer PCBs are usually devoted to ground planes. A ground plane helps distribute heat and reduces electromagnetic interference (EMI) noise pickup. Take care to physically separate digital and analog grounds, paying attention to the flow of the ground current. For more detailed information, see *Circuit Board Layout Techniques*.
- In order to reduce parasitic coupling, run the input traces as far away from the supply or output traces as possible. If these traces cannot be kept separate, crossing the sensitive trace perpendicular is much better as opposed to in parallel with the noisy trace.
- Place the external components as close to the device as possible. As illustrated in Figure 45, keeping R_F and R_G close to the inverting input minimizes parasitic capacitance on the inverting input.
- Keep the length of input traces as short as possible. Always remember that the input traces are the most sensitive part of the circuit.
- Consider a driven, low-impedance guard ring around the critical traces. A guard ring can significantly reduce leakage currents from nearby traces that are at different potentials.
- Cleaning the PCB following board assembly is recommended for best performance.
- Any precision integrated circuit can experience performance shifts resulting from moisture ingress into the plastic package. Following any aqueous PCB cleaning process, baking the PCB assembly is recommended to remove moisture introduced into the device packaging during the cleaning process. A low-temperature, post-cleaning bake at 85°C for 30 minutes is sufficient for most circumstances.



11.2 Layout Example

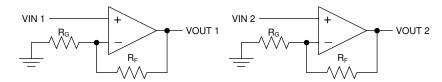


Figure 44. Schematic Representation for Figure 45

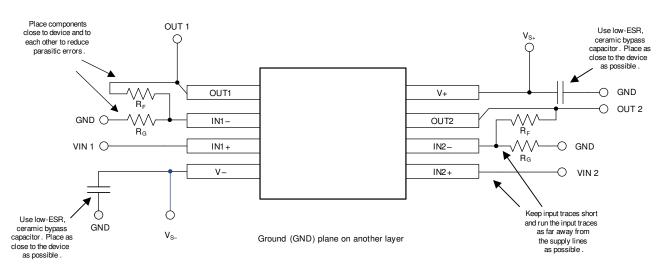


Figure 45. Layout Example



12 Device and Documentation Support

12.1 Documentation Support

12.1.1 Related Documentation

Texas Instruments, TLVx313 Low-Power, Rail-to-Rail In/Out, 500-µV Typical Offset, 1-MHz Operational Amplifier for Cost-Sensitive Systems

Texas Instruments, TLVx314 3-MHz, Low-Power, Internal EMI Filter, RRIO, Operational Amplifier

Texas Instruments, EMI Rejection Ratio of Operational Amplifiers

Texas Instruments, QFN/SON PCB Attachment

Texas Instruments, Quad Flatpack No-Lead Logic Packages

Texas Instruments, Circuit Board Layout Techniques

Texas Instruments, Single-Ended Input to Differential Output Conversion Circuit Reference Design

12.2 Related Links

The table below lists quick access links. Categories include technical documents, support and community resources, tools and software, and quick access to order now.

PARTS	PRODUCT FOLDER	ORDER NOW	TECHNICAL DOCUMENTS	TOOLS & SOFTWARE	SUPPORT & COMMUNITY	
TLV9051/S	Click here	Click here	Click here	Click here	Click here	
TLV9052/S	Click here	Click here	Click here	Click here	Click here	
TLV9054/S	Click here	Click here	Click here	Click here	Click here	

Table 2. Related Links

12.3 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

12.4 Community Resources

TI E2E[™] support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

12.5 Trademarks

E2E is a trademark of Texas Instruments. Bluetooth is a registered trademark of Bluetooth SIG, Inc. All other trademarks are the property of their respective owners.

12.6 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

12.7 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.



13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the mostcurrent data available for the designated devices. This data is subject to change without notice and without revision of this document. For browser-based versions of this data sheet, see the left-hand navigation pane.



10-Dec-2020

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TLV9051IDBVR	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	T51D	Samples
TLV9051IDCKR	ACTIVE	SC70	DCK	5	3000	RoHS & Green	SN	Level-2-260C-1 YEAR	-40 to 125	T51	Samples
TLV9051IDPWR	ACTIVE	X2SON	DPW	5	3000	RoHS & Green	NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	FH	Samples
TLV9051SIDBVR	ACTIVE	SOT-23	DBV	6	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	T51S	Samples
TLV9052IDDFR	ACTIVE	SOT-23-THIN	DDF	8	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	T052	Samples
TLV9052IDGKR	ACTIVE	VSSOP	DGK	8	2500	RoHS & Green	NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	1PWX	Samples
TLV9052IDR	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	TL9052	Samples
TLV9052IDSGR	ACTIVE	WSON	DSG	8	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	9052	Samples
TLV9052IPWR	ACTIVE	TSSOP	PW	8	2000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	TL9052	Samples
TLV9052SIDGSR	ACTIVE	VSSOP	DGS	10	2500	RoHS & Green	NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	T052	Samples
TLV9052SIRUGR	ACTIVE	X2QFN	RUG	10	3000	RoHS & Green	NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	FPF	Samples
TLV9054IDR	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	TLV9054D	Samples
TLV9054IPWR	ACTIVE	TSSOP	PW	14	2000	RoHS & Green	SN	Level-2-260C-1 YEAR	-40 to 125	T9054PW	Samples
TLV9054IRTER	ACTIVE	WQFN	RTE	16	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	T54RT	Samples
TLV9054IRUCR	ACTIVE	QFN	RUC	14	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	1FF	Samples
TLV9054SIRTER	ACTIVE	WQFN	RTE	16	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	T9054S	Samples

⁽¹⁾ The marketing status values are defined as follows: **ACTIVE:** Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.



10-Dec-2020

⁽²⁾ RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

⁽⁵⁾ Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

⁽⁶⁾ Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

PACKAGE MATERIALS INFORMATION

www.ti.com

Texas Instruments

TAPE AND REEL INFORMATION





QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TLV9051IDBVR	SOT-23	DBV	5	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TLV9051IDCKR	SC70	DCK	5	3000	178.0	9.0	2.4	2.5	1.2	4.0	8.0	Q3
TLV9051IDPWR	X2SON	DPW	5	3000	178.0	8.4	0.91	0.91	0.5	2.0	8.0	Q2
TLV9051SIDBVR	SOT-23	DBV	6	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TLV9052IDDFR	SOT- 23-THIN	DDF	8	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TLV9052IDGKR	VSSOP	DGK	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
TLV9052IDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TLV9052IDSGR	WSON	DSG	8	3000	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
TLV9052IPWR	TSSOP	PW	8	2000	330.0	12.4	7.0	3.6	1.6	8.0	12.0	Q1
TLV9052SIDGSR	VSSOP	DGS	10	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
TLV9052SIRUGR	X2QFN	RUG	10	3000	178.0	8.4	1.75	2.25	0.56	4.0	8.0	Q1
TLV9054IDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
TLV9054IPWR	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
TLV9054IRTER	WQFN	RTE	16	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2
TLV9054IRUCR	QFN	RUC	14	3000	180.0	9.5	2.16	2.16	0.5	4.0	8.0	Q2
TLV9054SIRTER	WQFN	RTE	16	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2

TEXAS INSTRUMENTS

www.ti.com

PACKAGE MATERIALS INFORMATION

30-Dec-2020



Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TLV9051IDBVR	SOT-23	DBV	5	3000	210.0	185.0	35.0
TLV9051IDCKR	SC70	DCK	5	3000	190.0	190.0	30.0
TLV9051IDPWR	X2SON	DPW	5	3000	205.0	200.0	33.0
TLV9051SIDBVR	SOT-23	DBV	6	3000	210.0	185.0	35.0
TLV9052IDDFR	SOT-23-THIN	DDF	8	3000	210.0	185.0	35.0
TLV9052IDGKR	VSSOP	DGK	8	2500	366.0	364.0	50.0
TLV9052IDR	SOIC	D	8	2500	853.0	449.0	35.0
TLV9052IDSGR	WSON	DSG	8	3000	210.0	185.0	35.0
TLV9052IPWR	TSSOP	PW	8	2000	853.0	449.0	35.0
TLV9052SIDGSR	VSSOP	DGS	10	2500	366.0	364.0	50.0
TLV9052SIRUGR	X2QFN	RUG	10	3000	205.0	200.0	33.0
TLV9054IDR	SOIC	D	14	2500	853.0	449.0	35.0
TLV9054IPWR	TSSOP	PW	14	2000	366.0	364.0	50.0
TLV9054IRTER	WQFN	RTE	16	3000	367.0	367.0	35.0
TLV9054IRUCR	QFN	RUC	14	3000	205.0	200.0	30.0
TLV9054SIRTER	WQFN	RTE	16	3000	367.0	367.0	35.0

DCK (R-PDSO-G5)

PLASTIC SMALL-OUTLINE PACKAGE



- NOTES: A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
 - D. Falls within JEDEC MO-203 variation AA.



LAND PATTERN DATA



NOTES:

- A. All linear dimensions are in millimeters.B. This drawing is subject to change without notice.
- C. Customers should place a note on the circuit board fabrication drawing not to alter the center solder mask defined pad.
- D. Publication IPC-7351 is recommended for alternate designs.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC-7525 for other stencil recommendations.



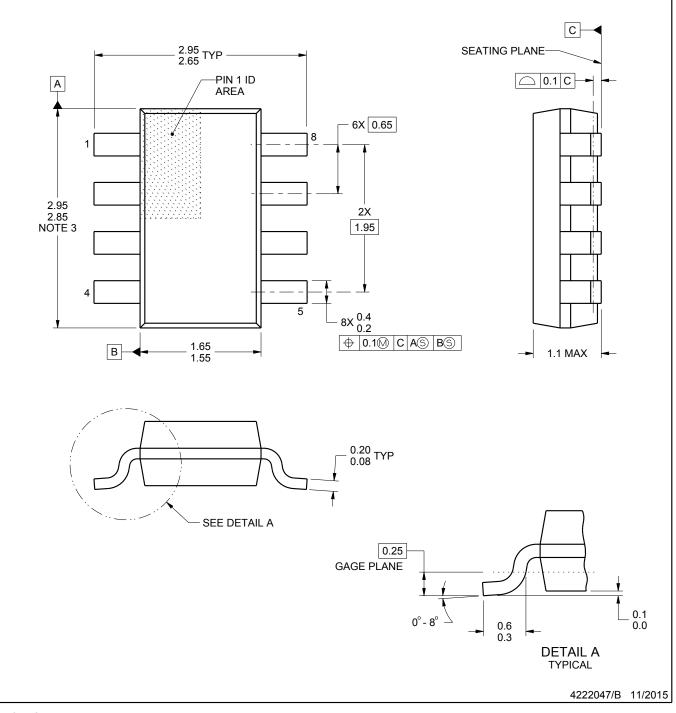
DDF0008A



PACKAGE OUTLINE

SOT-23 - 1.1 mm max height

PLASTIC SMALL OUTLINE



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice. 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.

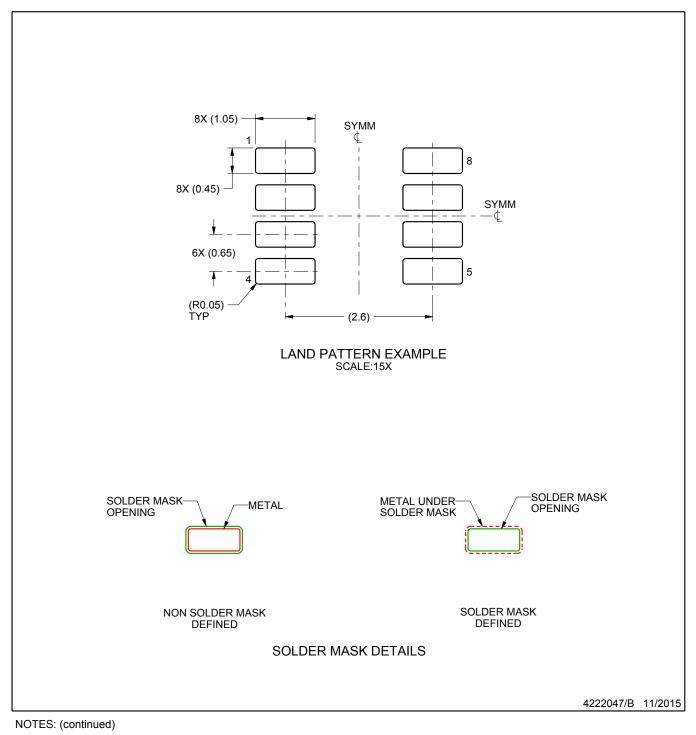


DDF0008A

EXAMPLE BOARD LAYOUT

SOT-23 - 1.1 mm max height

PLASTIC SMALL OUTLINE



4. Publication IPC-7351 may have alternate designs.

5. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

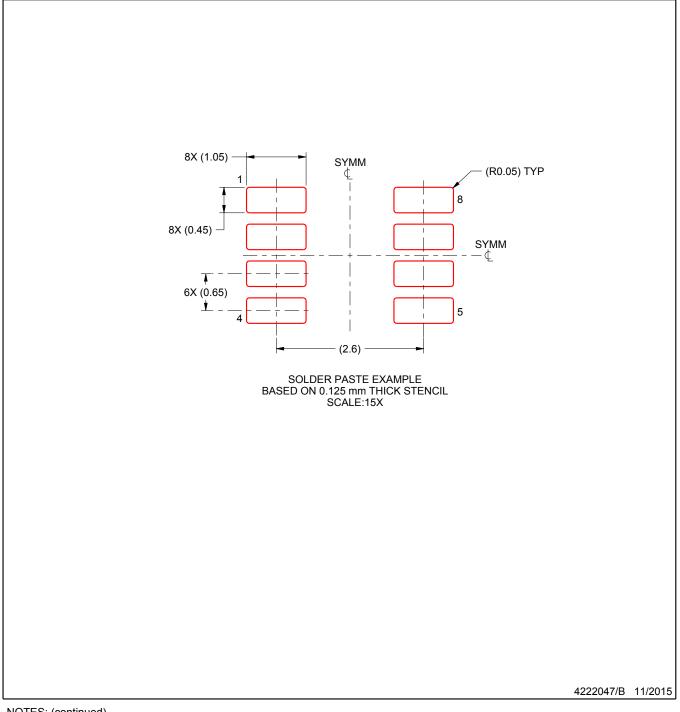


DDF0008A

EXAMPLE STENCIL DESIGN

SOT-23 - 1.1 mm max height

PLASTIC SMALL OUTLINE



NOTES: (continued)

- 6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 7. Board assembly site may have different recommendations for stencil design.



MECHANICAL DATA



- A. All linear almensions are in millimeters. Dimensioning and tolerancing per A B. This drawing is subject to change without notice.
 - C. Quad Flatpack, No-leads (QFN) package configuration.
 - The package thermal pad must be soldered to the board for thermal and mechanical performance. See the Product Data Sheet for details regarding the exposed thermal pad dimensions.
 - E. Falls within JEDEC MO-220.



RTE (S-PWQFN-N16)

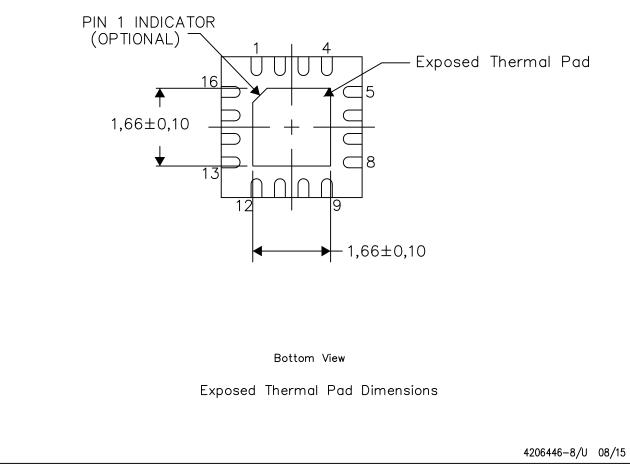
PLASTIC QUAD FLATPACK NO-LEAD

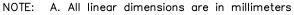
THERMAL INFORMATION

This package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. The thermal pad must be soldered directly to the printed circuit board (PCB). After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For information on the Quad Flatpack No-Lead (QFN) package and its advantages, refer to Application Report, QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271. This document is available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.

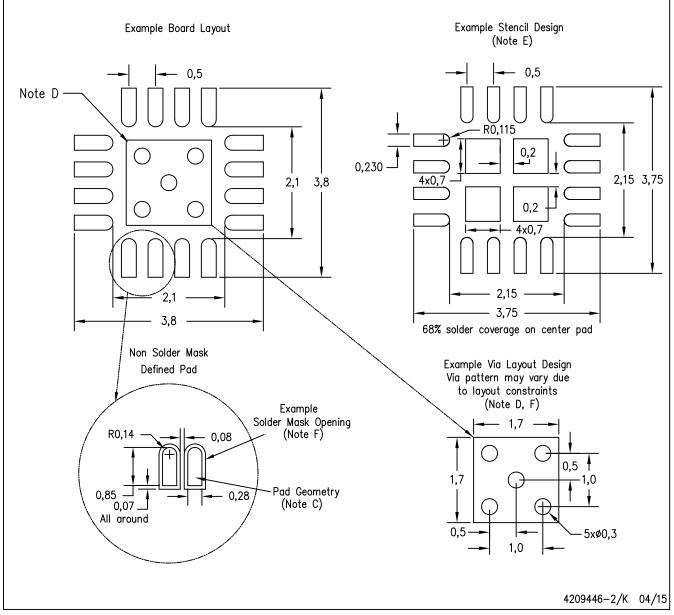






RTE (S-PWQFN-N16)

PLASTIC QUAD FLATPACK NO-LEAD



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. This package is designed to be soldered to a thermal pad on the board. Refer to Application Note, Quad Flat-Pack Packages, Texas Instruments Literature No. SLUA271, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com http://www.ti.com.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
- F. Customers should contact their board fabrication site for minimum solder mask web tolerances between signal pads.



DBV0006A



PACKAGE OUTLINE

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.2. This drawing is subject to change without notice.3. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.

- 4. Leads 1,2,3 may be wider than leads 4,5,6 for package orientation. 5. Refernce JEDEC MO-178.



DBV0006A

EXAMPLE BOARD LAYOUT

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



DBV0006A

EXAMPLE STENCIL DESIGN

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

9. Board assembly site may have different recommendations for stencil design.



DBV0005A



PACKAGE OUTLINE

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice. 3. Refernce JEDEC MO-178.

- 4. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.



DBV0005A

EXAMPLE BOARD LAYOUT

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



NOTES: (continued)

5. Publication IPC-7351 may have alternate designs.

6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



DBV0005A

EXAMPLE STENCIL DESIGN

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



NOTES: (continued)

7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

8. Board assembly site may have different recommendations for stencil design.



DGS0010A



PACKAGE OUTLINE

VSSOP - 1.1 mm max height

SMALL OUTLINE PACKAGE



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice. 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-187, variation BA.



DGS0010A

EXAMPLE BOARD LAYOUT

VSSOP - 1.1 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



DGS0010A

EXAMPLE STENCIL DESIGN

VSSOP - 1.1 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

9. Board assembly site may have different recommendations for stencil design.



^{8.} Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

GENERIC PACKAGE VIEW

X2SON - 0.4 mm max height PLASTIC SMALL OUTLINE - NO LEAD



Images above are just a representation of the package family, actual package may vary. Refer to the product data sheet for package details.



4211218-3/D

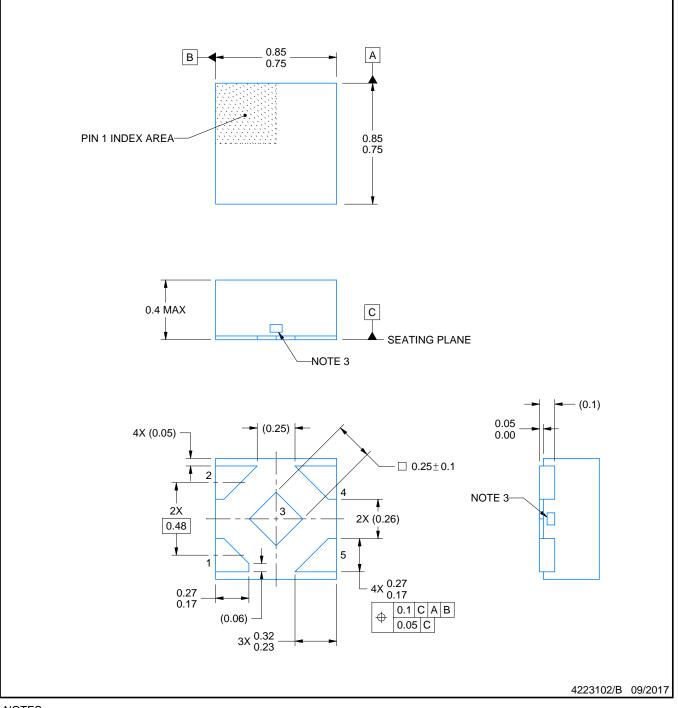
DPW0005A



PACKAGE OUTLINE

X2SON - 0.4 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.2. This drawing is subject to change without notice.
- 3. The size and shape of this feature may vary.

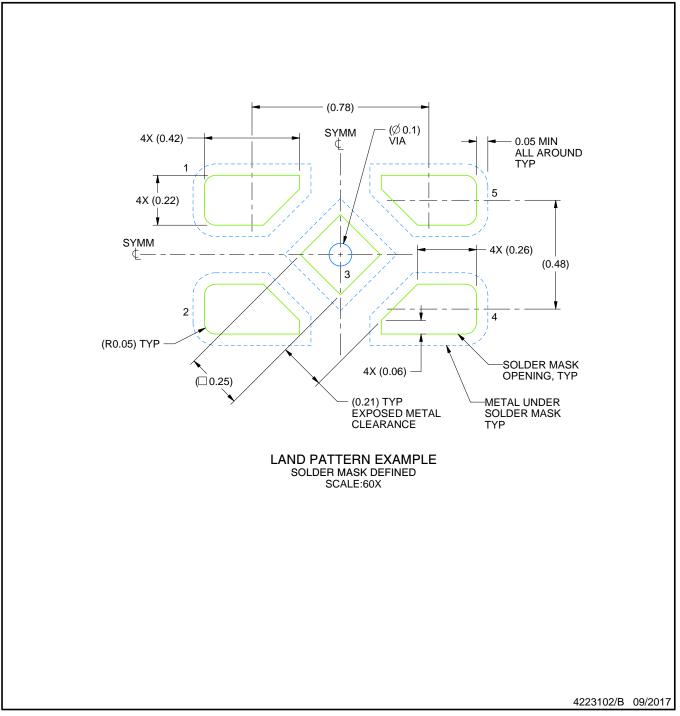


DPW0005A

EXAMPLE BOARD LAYOUT

X2SON - 0.4 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



NOTES: (continued)

4. This package is designed to be soldered to a thermal pad on the board. For more information, refer to QFN/SON PCB application note in literature No. SLUA271 (www.ti.com/lit/slua271).

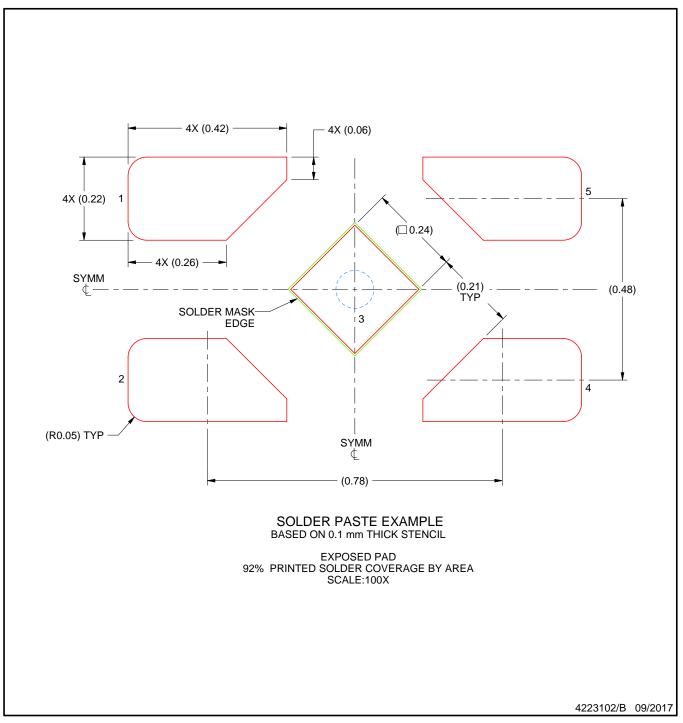


DPW0005A

EXAMPLE STENCIL DESIGN

X2SON - 0.4 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



NOTES: (continued)

5. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



D (R-PDSO-G14)

PLASTIC SMALL OUTLINE



NOTES: A. All linear dimensions are in inches (millimeters).

- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AB.





NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
 E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



PW (R-PDSO-G14)

PLASTIC SMALL OUTLINE



A. An integration of the information o

Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.

Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.

E. Falls within JEDEC MO-153





NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



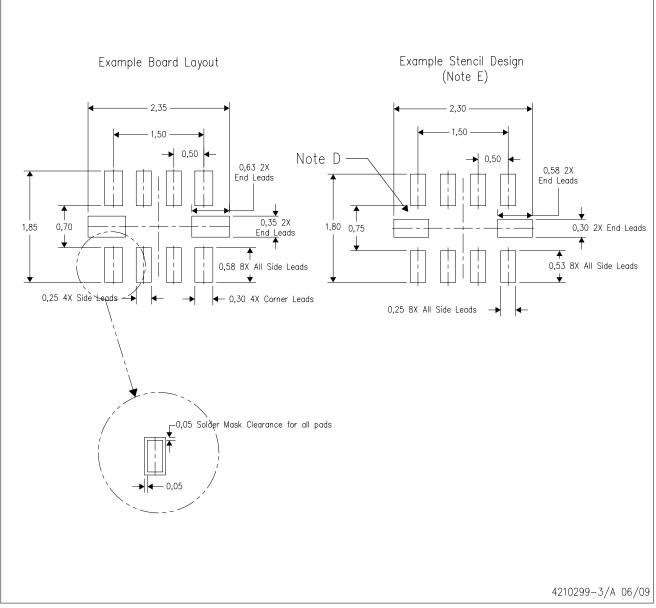
MECHANICAL DATA



B. This drawing is subject to change without notice.
C. QFN (Quad Flatpack No-Lead) package configuration.
D. This package complies to JEDEC MO-288 variation X2EFD.



RUG (R-PQFP-N10)



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Customers should contact their board fabrication site for minimum solder mask web tolerances between signal pads.
- E. Maximum stencil thickness 0,127 mm (5 mils). All linear dimensions are in millimeters.
- F. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
- G. Side aperture dimensions over-print land for acceptable area ratio > 0.66. Customer may reduce side aperture dimensions if stencil manufacturing process allows for sufficient release at smaller opening.



D0008A



PACKAGE OUTLINE

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



NOTES:

1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.

- 2. This drawing is subject to change without notice.
- 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
- 4. This dimension does not include interlead flash.
- 5. Reference JEDEC registration MS-012, variation AA.



D0008A

EXAMPLE BOARD LAYOUT

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



D0008A

EXAMPLE STENCIL DESIGN

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

9. Board assembly site may have different recommendations for stencil design.



DGK (S-PDSO-G8)

PLASTIC SMALL-OUTLINE PACKAGE



NOTES: A. All linear dimensions are in millimeters.

B. This drawing is subject to change without notice.

Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 per end.

- D Body width does not include interlead flash. Interlead flash shall not exceed 0.50 per side.
- E. Falls within JEDEC MO-187 variation AA, except interlead flash.



DGK (S-PDSO-G8)

PLASTIC SMALL OUTLINE PACKAGE



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



DSG 8

2 x 2, 0.5 mm pitch

GENERIC PACKAGE VIEW

WSON - 0.8 mm max height

PLASTIC SMALL OUTLINE - NO LEAD

This image is a representation of the package family, actual package may vary. Refer to the product data sheet for package details.





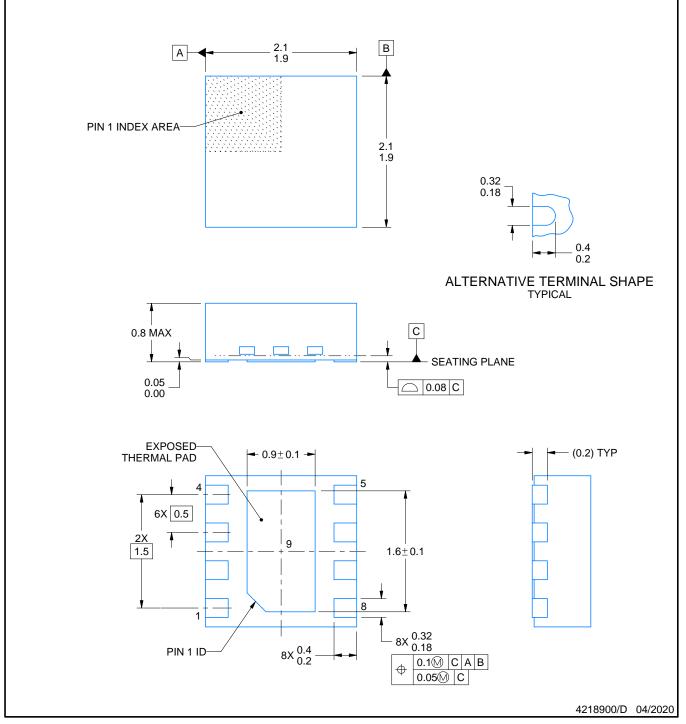
DSG0008A



PACKAGE OUTLINE

WSON - 0.8 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.

3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.

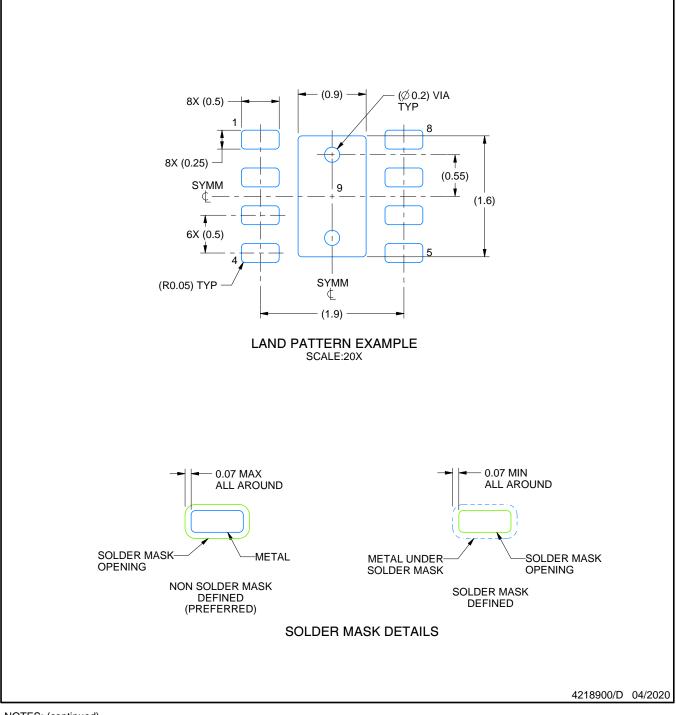


DSG0008A

EXAMPLE BOARD LAYOUT

WSON - 0.8 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



NOTES: (continued)

 This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).

 Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.

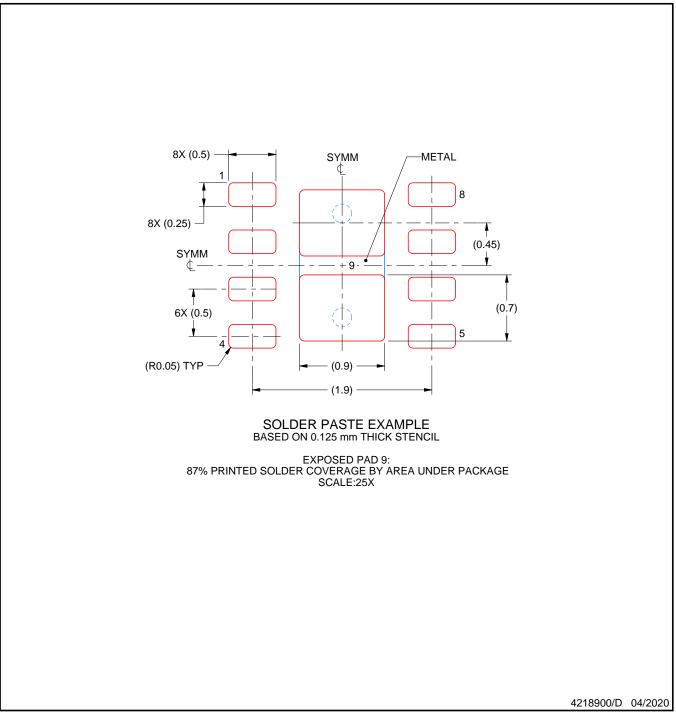


DSG0008A

EXAMPLE STENCIL DESIGN

WSON - 0.8 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



PW0008A



PACKAGE OUTLINE

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice. 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153, variation AA.



PW0008A

EXAMPLE BOARD LAYOUT

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



PW0008A

EXAMPLE STENCIL DESIGN

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

9. Board assembly site may have different recommendations for stencil design.



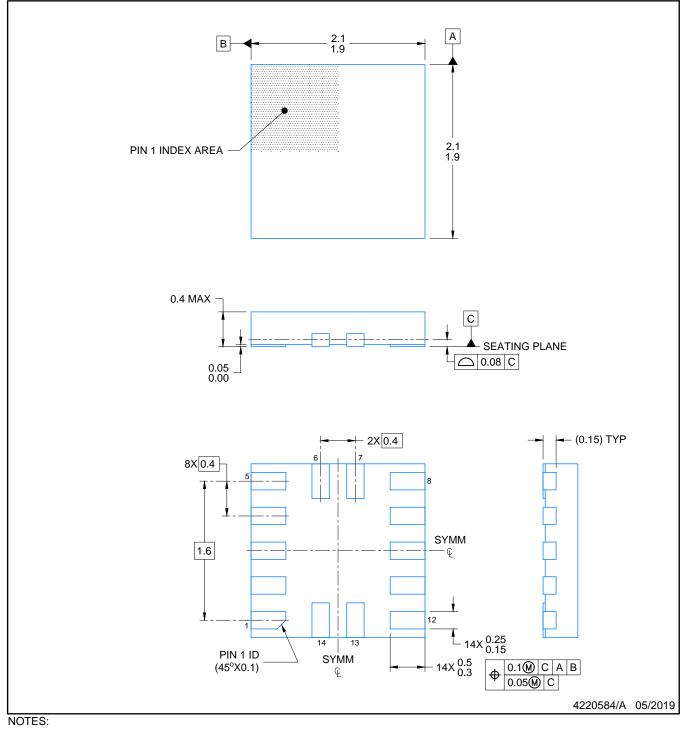
^{8.} Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

RUC0014A

PACKAGE OUTLINE

X2QFN - 0.4 mm max height

PLASTIC QUAD FLAT PACK- NO LEAD



- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.

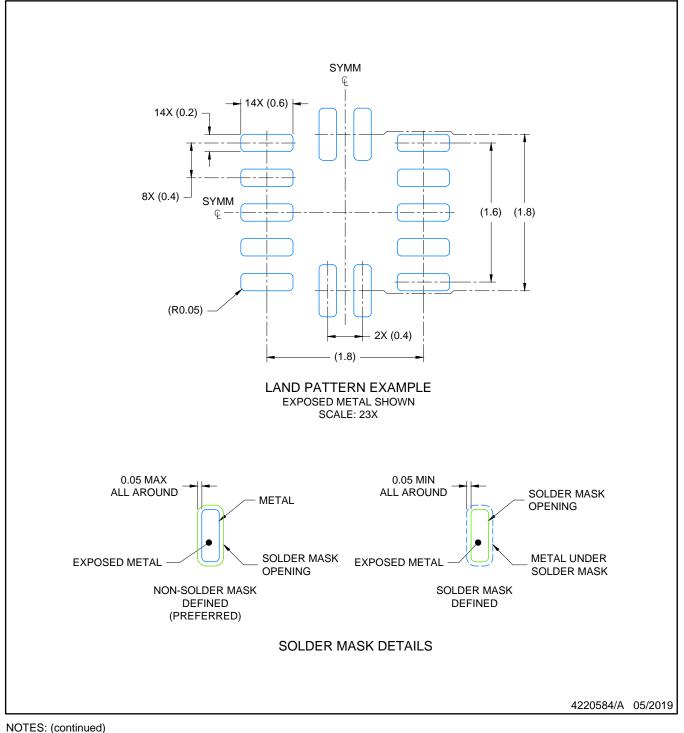


RUC0014A

EXAMPLE BOARD LAYOUT

X2QFN - 0.4 mm max height

PLASTIC QUAD FLAT PACK- NO LEAD



3. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).

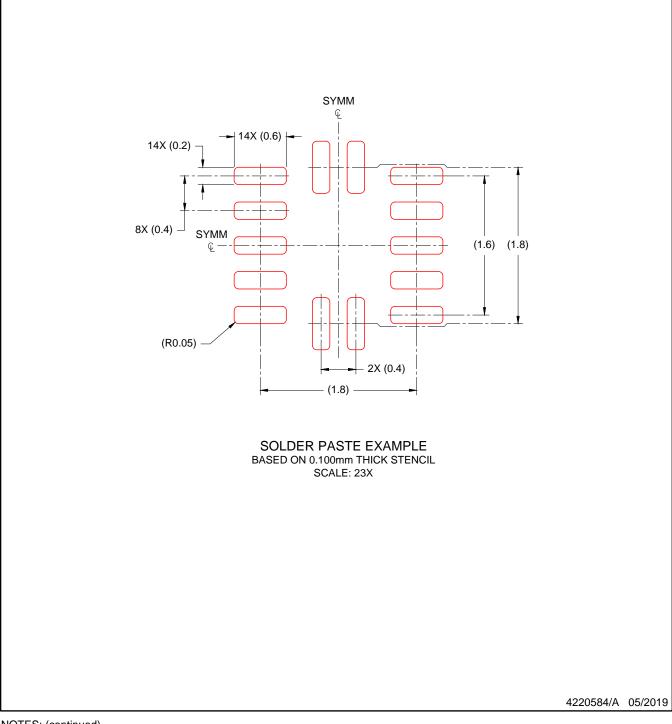


RUC0014A

EXAMPLE STENCIL DESIGN

X2QFN - 0.4 mm max height

PLASTIC QUAD FLAT PACK- NO LEAD



NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



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